

0.8A, 200V - 600V Miniature Glass Passivated Fast Recovery Surface Mount Bridge Rectifier

FEATURES

- Ideal for automated placement
- Reliable low cost construction utilizing molded plastic technique
- High surge current capability
- Small size, simple installation
- UL Recognized File # E-326243
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

-			_IC		-	^		
Δ	v	"		Δ		C D	N	-

- Switching mode power supply (SMPS)
- Lighting application

MECHANICAL DATA

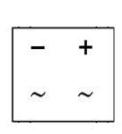
- Case: TO-269AA (MBS)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.12g (approximately)

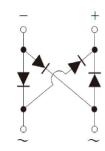
KEY PARAMETERS					
PARAMETER VALUE UNIT					
I _{F(AV)}	0.8	Α			
V_{RRM}	200 - 600	V			
I _{FSM}	30	Α			
T_{JMAX}	150	°C			
Package	TO-269AA (MBS)				
Configuration	Quad				





TO-269AA (MBS)





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	RMB2S	RMB4S	RMB6S	UNIT	
Marking code on the device		RMB2S	RMB4S	RMB6S		
Repetitive peak reverse voltage	V_{RRM}	200	400	600	V	
Reverse voltage, total rms value	$V_{R(RMS)}$	140	280	420	V	
Maximum DC blocking voltage	V_{DC}	200	400	600	V	
Maximum average forward current 60Hz sine wave resistance load on glass-epoxy P.C.B.	ı		0.5		Α	
Maximum average forward current 60Hz sine wave resistance load on aluminum substrate	I _{F(AV)}		0.8		Α	
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}		30		А	
Rating for fusing (t<8.3ms)	I ² t	3.74		A ² s		
Junction temperature	TJ		- 55 to +150		°C	
Storage temperature	T _{STG}		- 55 to +150		°C	



THERMAL PERFORMANCE						
PARAMETER	SYMBOL	TYP	UNIT			
Junction-to-ambient thermal resistance per diode	$R_{\Theta JA}$	85	°C/W			

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT	
Forward voltage per diode (1)	I _F = 0.4A, T _J = 25°C	V _F	-	1	V	
	T _J = 25°C		-	5	μA	
Reverse current @ rated V _R per diode ⁽²⁾	T _J = 125°C	- I _R	-	100	μA	
Junction capacitance	1 MHz, V _R =4.0V	Сл	13	-	pF	
Reverse recovery time	I _F =0.5A,I _R =1.0A I _{RR} =0.25A	t _{rr}	-	150	ns	

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION						
PART NO.	PART NO. SUFFIX(*)	PACKING CODE	PACKING CODE SUFFIX	PACKAGE	PACKING	
RMBxS		RC	0	MBS	3,000 / 13" Paper reel	
(Note 1, 2)	Н	MC	G		3,000 / 13" Plastic reel	

Notes:

- 1. "x" defines voltage from 200V (RMB2S) to 600V (RMB6S)
- 2. Whole series with green compound (halogen-free)
- *: Optional available

EXAMPLE						
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION	
RMB2SHRCG	RMB2S	Н	RC	G	Green compound AEC-Q101 qualified	



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

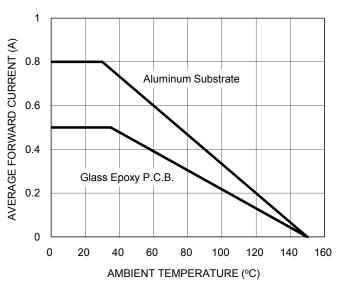


Fig.2 Typical Junction Capacitance

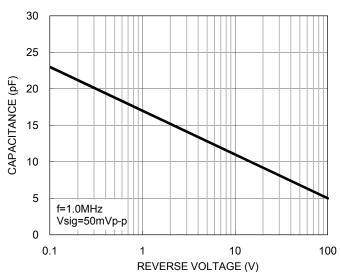


Fig.3 Typical Reverse Characteristics

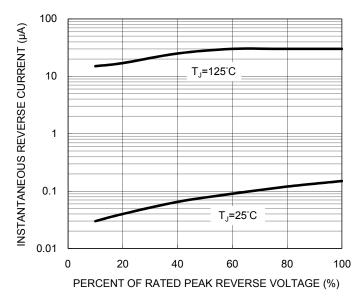
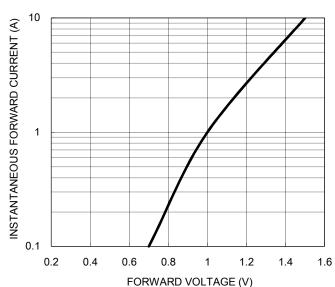


Fig.4 Typical Forward Characteristics





CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.5 Maximum Non-repetitive Forward Surge Current

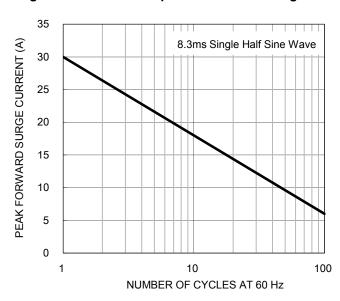
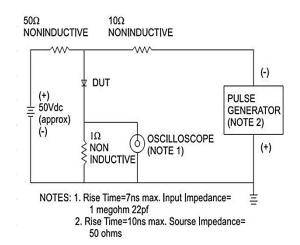
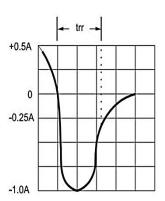


Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram



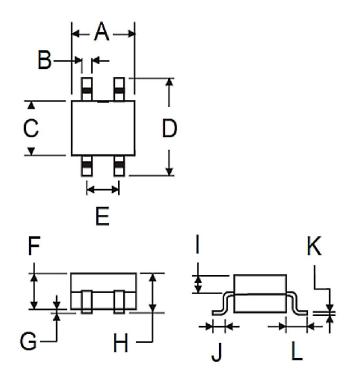


4



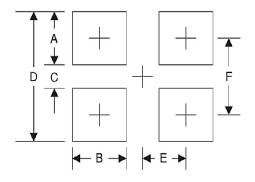
PACKAGE OUTLINE DIMENSIONS

TO-269AA (MBS)



r					
DIM.	Unit	(mm)	Unit (inch)		
DIWI.	Min	Max	Min	Max	
Α	4.50	4.90	0.177	0.193	
В	0.56	0.84	0.022	0.033	
С	3.60	5.00	0.142	0.197	
D	-	6.90	-	0.272	
Е	2.20	2.60	0.087	0.102	
F	2.30	2.70	0.091	0.106	
G	-	0.20	-	0.008	
Н	-	2.90	-	0.114	
I	0.95	1.53	0.037	0.060	
J	0.70	1.10	0.028	0.043	
K	0.15	0.35	0.006	0.014	
L	1.10	2.12	0.043	0.083	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
А	1.70	0.067
В	0.90	0.035
С	4.40	0.173
D	8.10	0.319
E	1.30	0.051
F	6.30	0.248

MARKING DIAGRAM



P/N = Marking Code YW = Date Code F = Factory Code



Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bridge Rectifiers category:

Click to view products by Taiwan Semiconductor manufacturer:

Other Similar products are found below:

MB2510 MB252 MB356G MB358G GBJ1504-BP GBU15J-BP GBU15K-BP GBU4A-BP GBU6B-E3/45 GSIB680-E3/45 DB101-BP DF01 DF10SA-E345 KBPC50-10S RS405GL-BP G5SBA60-E3/51 GBU10J-BP GBU6M GBU8D-BP GBU8J-BP GSIB1520-E3/45 2KBB10 36MB140A TB102M MB1510 MB258 MB6M-G MB86 TL401G MDA920A2 TU602 TU810 MP501W-BP BR101-BP BR84DTP204 BU2008-E3/51 36MB100A KBPC10/15/2501WP KBPC25-02 VS-2KBB60 DF06SA-E345 DF1510S VS-40MT160PAPBF W02M GBL02-E3/45 GBU4G-BP GBJ2506-BP GBU6B-E3/51 GSIB15A80-E3/45 DB104-BP